ABSTRACT OF THE DISCLOSURE

A semiconductor memory device is provided, which comprising a memory cell array comprising a two-value memory region and a multi-value memory region, in which the two-value memory region comprises a plurality of memory cells each storing 1-bit data and the multi-value memory region comprises a plurality of memory cells each storing 2 or more-bit data, and a sense amplifier section common to data read of the two-value memory region and data read of the multi-value memory region, for reading data stored in a selected memory cell by comparing a potential of the selected memory cell with a reference potential.